



#6/A  
4-18-02  
Melloni

In re Application of

Nakagawa, K.

Serial No.: 09/688,203 ✓

Group Art Unit: 2823

Filed: October 16, 2000 ✓

Examiner: Collins, D.

For: METHOD OF MANUFACTURING SEMICONDUCTOR MEMORY DEVICE

Honorable Assistant Commissioner of Patents  
Washington, D.C. 20231

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APR 15 2002  
TECHNOLOGY CENTER 2800

**AMENDMENT UNDER 37 C.F.R. §1.111**

Sir:

In response to the Office Action dated January 16, 2002, please amend the above-identified application as follows:

**IN THE CLAIMS:**

✓  
**Please cancel claims 7-12 without prejudice or disclaimer.**

**Please revise claims 1-4 to read as follows:**

AI  
1. (Amended) A method of manufacturing a semiconductor memory device capable of electrically writing and erasing data, said semiconductor memory device having a plurality of cell transistors for storing data, each of said cell transistors having a floating gate electrode and a control gate electrode, and a plurality of select transistors for controlling and selecting said cell transistors, said method comprising:

before forming the control gate electrodes of said cell transistors, exposing a surface of a substrate directly above channel regions of said select transistors fabricated in